2SK2885(L), 2SK2885(S)

Silicon N Channel MOS FET High Speed Power Switching

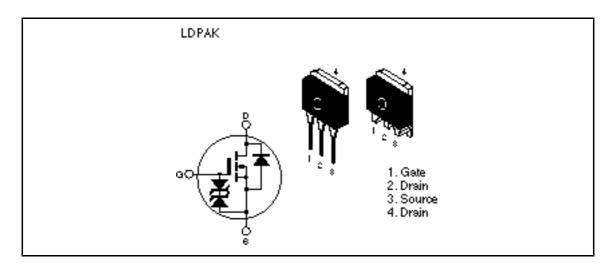
HITACHI

ADE-208-545 A 2nd. Edition

Features

- Low on-resistance $R_{DS(on)} = 10m \quad typ.$
- 4V gate drive devices.
- · High speed switching

Outline





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Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

| Item | Symbol | Ratings | Unit |
|---|--------------------------|-------------|------|
| Drain to source voltage | V _{DSS} 30 | | V |
| Gate to source voltage | $V_{\rm GSS}$ | ±20 | V |
| Drain current | I _D | 45 | А |
| Drain peak current | I _{D(pulse)} *1 | 180 | А |
| Body to drain diode reverse drain current | I _{DR} | 45 | А |
| Channel dissipation | Pch*2 | 75 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW 10µs, duty cycle 1 %

2. Value at Tc = 25°C

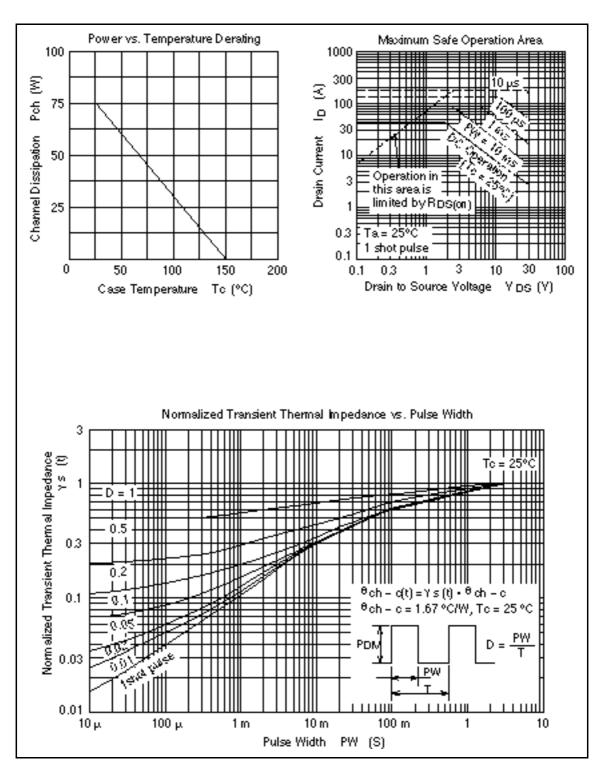
Electrical Characteristics ($Ta = 25^{\circ}C$)

| Item | Symbol | Min | Тур | Max | Unit | Test Conditions |
|---|---------------------|-----|------|-----|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 30 | _ | _ | V | $I_{D} = 10 \text{mA}, V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±20 | _ | _ | V | $I_{G} = \pm 100 \mu A, V_{DS} = 0$ |
| Zero gate voltege drain current | I _{DSS} | _ | _ | 10 | μΑ | $V_{DS} = 30 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 16V, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.0 | _ | 2.0 | V | $I_{D} = 1 \text{mA}, V_{DS} = 10 \text{V}$ |
| Static drain to source on state | $R_{\text{DS(on)}}$ | _ | 10 | 14 | m | $I_D = 20A, V_{GS} = 10V^{*1}$ |
| resistance | R _{DS(on)} | _ | 15 | 25 | m | $I_D = 20A, V_{GS} = 4V^{*1}$ |
| Forward transfer admittance | y _{fs} | 20 | 30 | _ | S | $I_D = 20A, V_{DS} = 10V^{*1}$ |
| Input capacitance | Ciss | _ | 1550 | _ | pF | V _{DS} = 10V |
| Output capacitance | Coss | _ | 1050 | _ | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 230 | _ | pF | f = 1MHz |
| Turn-on delay time | $t_{d(on)}$ | _ | 20 | _ | ns | $V_{GS} = 10V, I_{D} = 20A$ |
| Rise time | t _r | _ | 370 | _ | ns | $R_{L} = 0.5$ |
| Turn-off delay time | $t_{d(off)}$ | _ | 170 | _ | ns | |
| Fall time | t _f | _ | 180 | _ | ns | _ |
| Body to drain diode forward voltage | V_{DF} | _ | 0.95 | _ | V | $I_{D} = 45A, V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t _{rr} | _ | 75 | _ | ns | $I_F = 45A, V_{GS} = 0$ diF/ dt = 50A/µs |

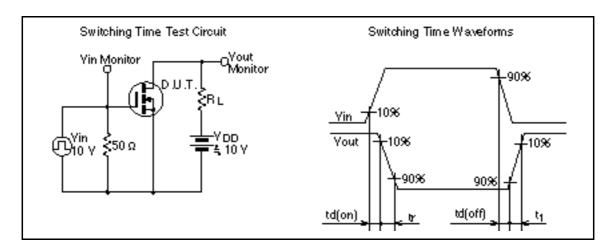
Note: 1. Pulse test

See characteristics curves of 2SK2737

Main Characteristics

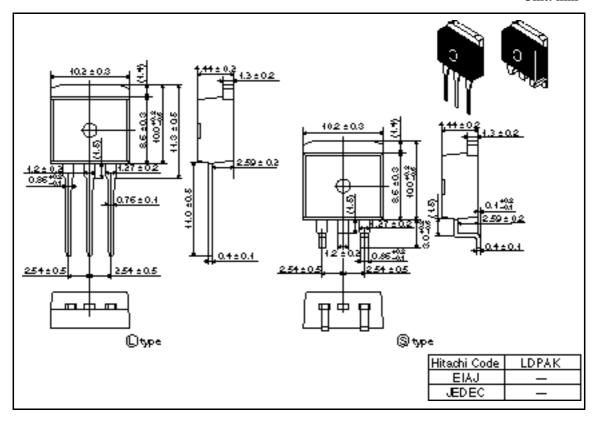


2SK2885(L), 2SK2885(S)



Package Dimensions

Unit: mm



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